Ref #	Hits	Search Query	DBs Default Plural Operator		Plurals	Time Stamp
S1	2	apparatus\$2 same (barrier:near2 (layer or film)):same trench\$2 same (dielectric:near2 (layer:or film)):same ((ion:near2:implant\$5) or dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 17:03
S2	1107	apparatus\$2 and (barrier near2 (layer or film)) and trench\$2 and (dielectric near2 (layer or film)) and ((ion near2 implant\$5) or dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:43
S3	5	apparatus\$2 same( (barrier near2 (layer or film)) and trench\$2 and (dielectric near2 (layer or film)) and ((ion near2 implant\$5) or dop\$3))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:05
S4	9	("5897368"   "6110817"   "6218303"   "6239021"   "6258695"   "6300236"   "6340633"   "6342447"   "6352938"   "2001/0010401").PN.	USPAT	OR	OFF	2004/09/10 16:07
S5	1373	apparatus\$2 near5 trench\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:12
S6	2500	apparatus\$2 with trench\$2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:12
S7	62	(apparatus\$2 with trench\$2 ) and (barrier near2 (layer or film)) and (dielectric near2 (layer or film))and ((ion near2 implant\$5) or dop\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 20:01
S8	108	isaac-stanetta.xa.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 16:29
59	4	"6713385"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 17:04

S10	3043	((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/08 09:16
S11	4	(438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.) and (apparatus\$2 with trench\$2 ) and (barrier near2 (layer or film)) and (dielectric near2 (layer or film))and ((ion near2 implant\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/09/10 20:01
S12	194	or dop\$3) apparatus same ((trench\$3 or groov\$3) near3 (silicon near2 (wafer\$1 or substrate\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 12:58
S13	30	S12 and (((ion near2 implant\$5) or dop\$3) same (dielectric or insulat\$3 or fill\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:05
S14	4230	apparatus same (((ion near2 implant\$5) or dop\$3) same (dielectric or insulat\$3 or fill\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:17
S15	46	S14 and ((trench\$3 or groov\$3) near3 (silicon near2 (wafer\$1 or substrate\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:09
S16	2764	(((ion near2 implant\$5) or dop\$3) near3 (dielectric or insulat\$3 or fill\$3)) same (trench\$3 or groov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 09:45
S17	383	S16 and apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:19

S18	360	S17 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:20
S19	1566	(((ion near2 implant\$5) or dop\$3) near3 (dielectric or insulat\$3)) same (trench\$3 or groov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:39
S20	232	S19 and apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:21
S21	221	S20 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 13:21
S22	1161	((ion near2 implant\$5) or dop\$3) near3 ((dielectric or insulat\$3) near2 (layer\$1 or film\$1)) same (trench\$3 or groov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 15:22
S23	154	S22 and apparatus	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/04 15:23
S24	3212	((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 13:29
S25	2089	S24 and (trench\$2 or groov\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:43
S26	2021	S25 and (((ion near2 implant\$5) or dop\$3) near5 ((trench\$2 or groov\$2) near2 fill\$3) or dielectric or insulat\$3 or fill\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:52

S27	1631	S26 and (planar\$7 or (cmp or (chemical near2 polish\$3)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:49
S28	367	S27 and nitrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:50
S29	2021	S25 and (((ion near2 implant\$5) or dop\$3) near ((trench\$2 or groov\$2) near2 fill\$3) or dielectric or insulat\$3 or fill\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/12 19:52
S30	3301	((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/18 11:45
S31	24	S30 and ((ion\$1 or (ion near implant\$5) or dop\$3) near3 ((dielectric or insulat\$3) near2 (trench\$2 or groov\$2 or apeture\$1)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/18 11:48
S32	3516	((438/221) or (438/296) or (438/359) or (438/424) or (438/449) or (438/527) or (438/528)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/08 09:16
S33	3082	(((ion near2 implant\$5) or dop\$3) near3 (dielectric or insulat\$3 or fill\$3)) same (trench\$3 or groov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 09:45
534	146	S32 and S33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 09:45
S35	13	S34 and ((high\$3 or increas\$3) near2 etch\$3 near rate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/08 09:46

S36	7024	((438/221) or (438/296) or (438/359) or (438/423) or (438/424) or (438/433) or (438/449) or (438/527) or (438/528) or (438/692) or (438/700)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 13:38
S37	144	S36 and ((((ion near2 implant\$5) or dop\$3) near3 (dielectric or insulat\$3)) same (trench\$3 or groov\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:46
S38	234	S36 and ((((ion near2 implant\$5) or dop\$3) near3 (dielectric or insulat\$3 or fill\$3)) same (trench\$3 or groov\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:46
S39	16205	"10" and (("CMP" or planar\$7) near5 (trench\$2 or groove\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:47
S40	97	S38 and (("CMP" or planar\$7) near5 (trench\$2 or groove\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/08 13:47

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S41	108	("3629023"	"3979239"	1	US-PGPUB;	OR	OFF	2005/12/08 13:48
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S42	0	("6969684")	.URPN.		USPAT	OR	OFF	2005/12/08 13:51

S43	2	("6514833"   "6576558").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/08 13:52
S44.	24	("4577395"   "4589193"   "4654120"   "4722910"   "5021355"   "5059550"   "5212106"   "5215937"   "5229316"   "5258332"   "5275965"   "5281550"   "5292683"   "5298110"   "5300447"   "5396096"   "5408116"   "5413945"   "5482878"   "5506168"   "5521422"   "5607875"   "5677229"   "5741738").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/08 13:56
S45	11	("6084276").URPN.	USPAT	OR	OFF	2005/12/08 13:58
S46	3.	("4571819"   "5316965"   "5616513").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/08 14:01
S47	15	("5902127").URPN.	USPAT	OR	OFF	2005/12/08 15:08
S48	249	(438/433).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/08 15:09
S49	3	("20020098661"   "20020137306"   "6221734").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/12/08 15:13